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a reflection layer which is formed on said light transmission layer, comprises a metal, and reflects lights emitted from said emission layer.

2. (Amended) A light-emitting semiconductor device comprising:

a substrate;

a plurality of semiconductor layers which comprise group III nitride group compound semiconductors and are laminated on said substrate by crystal growth;

an emission layer; and

a mirror surface comprising:

a reflection layer which comprises a metal and reflects lights emitted from said emission layer; and

a corrosion-resisting layer which is formed on said reflection layer and comprises at least one of a metal oxide and a ceramic.

5. (Amended) A light-emitting device using group III nitride group compound semiconductor according to claim 2, further comprising:

a light transmission layer which directly contacts said substrate, has luminous transparency, and comprises at least one material selected from a group consisting of metal oxides and ceramics,

wherein said reflection layer is formed by using at least one of aluminum (Al), Silver (Ag), and an alloy including at least one of these materials.

7. (Amended) A light-emitting device using group III nitride group compound semiconductor according to claim 2, further comprising:

a light transmission layer which contacts said substrate, has luminous transparency, and comprises at least one material selected from a group consisting of metal oxides and ceramics,

wherein a thickness of said reflection layer is in a range of 5 nm to 20  $\mu\text{m}$ .

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9. (Amended) A light-emitting device using group III nitride group compound semiconductor according to claim 2, further comprising:

a light transmission layer which contacts said substrate, has luminous transparency, and comprises at least one material selected from a group consisting of metal oxides and ceramics,

wherein said light transmission layer comprises at least one of  $\text{Al}_2\text{O}_3$ ,  $\text{TiO}_2$ ,  $\text{MgO}$ ,  $\text{MgCO}_3$ ,  $\text{Ta}_2\text{O}_5$ ,  $\text{ZnO}$ ,  $\text{In}_2\text{O}_3$ ,  $\text{SiO}_2$ ,  $\text{SnO}_2$ , and  $\text{ZrO}_2$ .

11. (Amended) A light-emitting device using group III nitride group compound semiconductor according to claim 5, wherein said light transmission layer comprises at least one of  $\text{Al}_2\text{O}_3$ ,  $\text{TiO}_2$ ,  $\text{MgO}$ ,  $\text{MgCO}_3$ ,  $\text{Ta}_2\text{O}_5$ ,  $\text{ZnO}$ ,  $\text{In}_2\text{O}_3$ ,  $\text{SiO}_2$ ,  $\text{SnO}_2$ , and  $\text{ZrO}_2$ .

13. (Amended) A light-emitting device using group III nitride group compound semiconductor according to claim 7, wherein said light transmission layer comprises least one of  $\text{Al}_2\text{O}_3$ ,  $\text{TiO}_2$ ,  $\text{MgO}$ ,  $\text{MgCO}_3$ ,  $\text{Ta}_2\text{O}_5$ ,  $\text{ZnO}$ ,  $\text{In}_2\text{O}_3$ ,  $\text{SiO}_2$ ,  $\text{SnO}_2$ , and  $\text{ZrO}_2$ .